

HSM126S

Silicon Schottky Barrier Diode for System Protection

HITACHI

Rev. 3
May. 1995

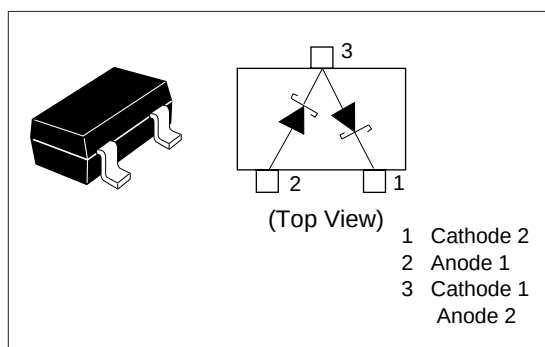
Features

- HSM126S which is connected in series configuration enable to protect electric systems from miss-operation against external + and – surge.
- Low V_F and low leakage current.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Mark	Package Code
HSM126S	S14	MPAK

Pin Arrangement



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$) ***

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	I_O^*	200	mA
Non-Repetitive peak forward surge current	I_{FSM}^{**}	2	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

* Sine wave, Two device total

** 50Hz half sine wave 1 pulse

*** Per one device

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	2.0	μA	$V_R = 5\text{ V}$
Forward voltage	V_F	—	—	0.35	V	$I_F = 10\text{ mA}$
Capacitance	C	—	40	—	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$

* Per one device

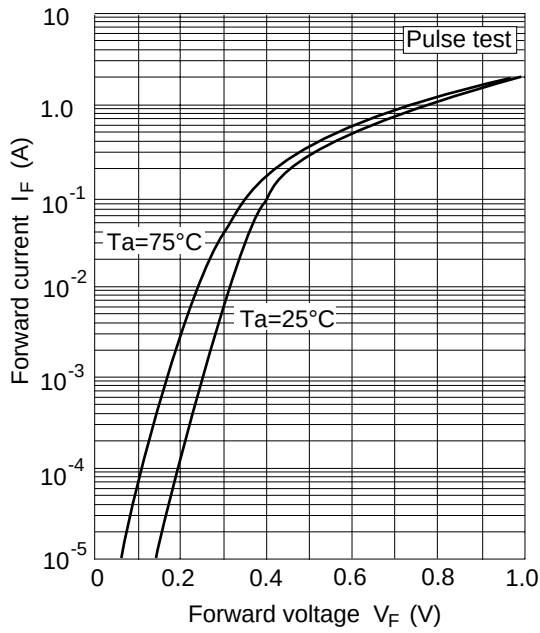


Fig.1 Forward current Vs. Forward voltage

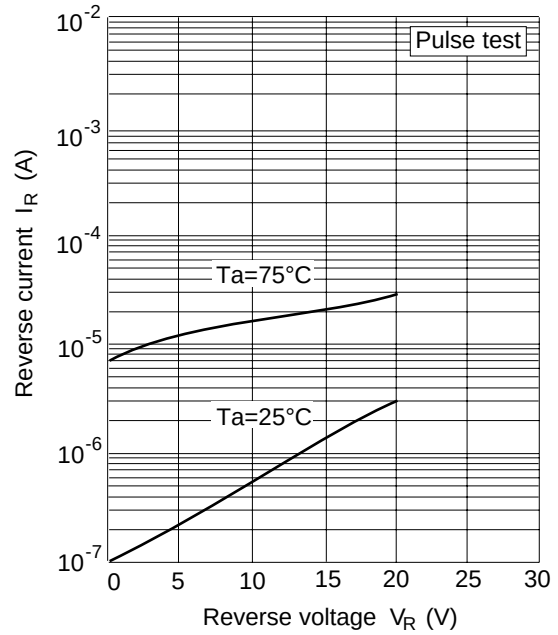


Fig.2 Reverse current Vs. Reverse voltage

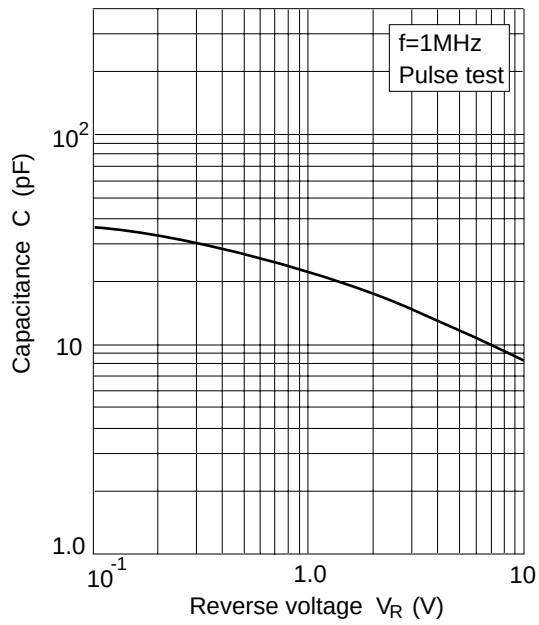
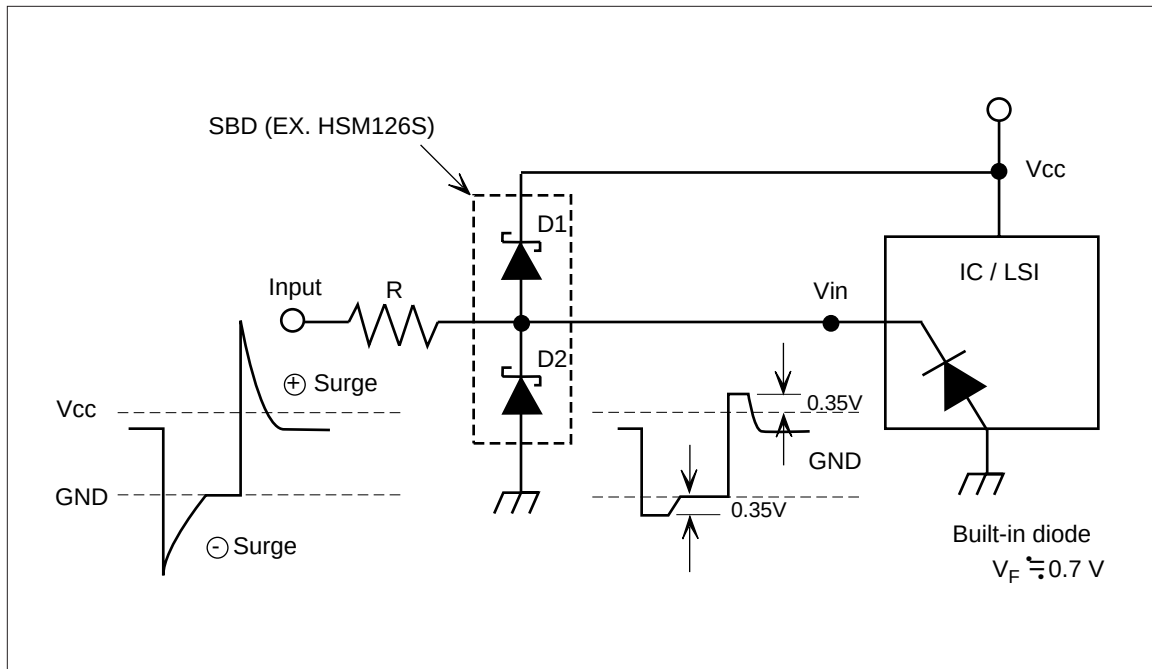


Fig.3 Capacitance Vs. Reverse voltage

Example of application circuit



Package Dimensions

Unit: mm

